

B-DOOR

[TERMINAL-[20020325.LOG]]

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- 2/4 - (C) WF1 / DERWENT
 AN - 1997-219045 [20]
 AP - JP19950218861 19950823
 PR - JP19950218861 19950828
 TI - III-V group compound semiconductor light emitting element - has P type layer whose composition contains indium, gallium, aluminium and zinc satisfying specific relation
 IW - GROUP COMPOUND SEMICONDUCTOR LIGHT EMIT ELEMENT P TYPE LAYER COMPOSITION CONTAIN INDIUM GALLIUM ALUMINIUM ZINC SATISFY SPECIFIC RELATED
 PA - (SUMO) SUMITOMO CHEM CO LTD
 --> PN - JP9064419 A 19970307 DW199720 H01L33/00 006pp
 IC - H01L21/205 ; H01L29/205 ; H01L33/00
 AB - J09064419 The element has a substrate (1) on which a buffer layer (2) is formed. A n-type layer (3) is arranged above the buffer layer. A pair of undoped layers (4,6) are arranged orderly on the n type layer between which a light emitting layer (5) is formed.
 - The undoped layers have a larger band width than the light emitting layer. A p type layer (7) is provided above one of the undoped layer. This has a composition $In_x Ga_y Al_z N$ where $x+y+z=1$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0.001 \leq z \leq 0.10$.
 - ADVANTAGE - Raises luminous efficiency.
 - (Dwg.1/2)